DATA SHEET

MB2374

Dual octal D-type flip-flop; positive-edge trigger (3-State)

Product specification

August 23, 1993

IC23

PHILIPS

16-bit D-type flip-flop; positive-edge trigger (3-State) MB2374

FEATURES

- Two 8-bit positive edge triggered registers
- Live insertion/extraction permitted
- Power-up 3-State
- Power-up reset
- Multiple V_{CC} and GND pins minimize switching noise
- 3-State output buffers
- Output capability: +64mA/–32mA
- Latch-up protection exceeds 500mA per Jedec Std 17
- ESD protection exceeds 2000V per MIL STD 883 Method 3015 and 200V per Machine Model

DESCRIPTION

The MB2374 high-performance BiCMOS device combines low static and dynamic power dissipation with high speed and high output drive.

The MB2374 has two 8-bit, edge triggered registers, with each register coupled to eight 3-State output buffers. The two sections of each register are controlled independently by the clock (nCP) and Output Enable ($n\overline{OE}$) control gates.

Each register is fully edge triggered. The state of each D input, one set-up time before the Low-to-High clock transition, is transferred to the corresponding flip-flop's Q output.

The 3-State output buffers are designed to drive heavily loaded 3-State buses, MOS memories, or MOS microprocessors. Each active-Low Output Enable ($n\overline{OE}$) controls all eight 3-State buffers for its register independent of the clock operation.

When $n\overline{OE}$ is Low, the stored data appears at the outputs for that register. When $n\overline{OE}$ is High, the outputs for that register are in the High-impedance "OFF" state, which means they will neither drive nor load the bus.

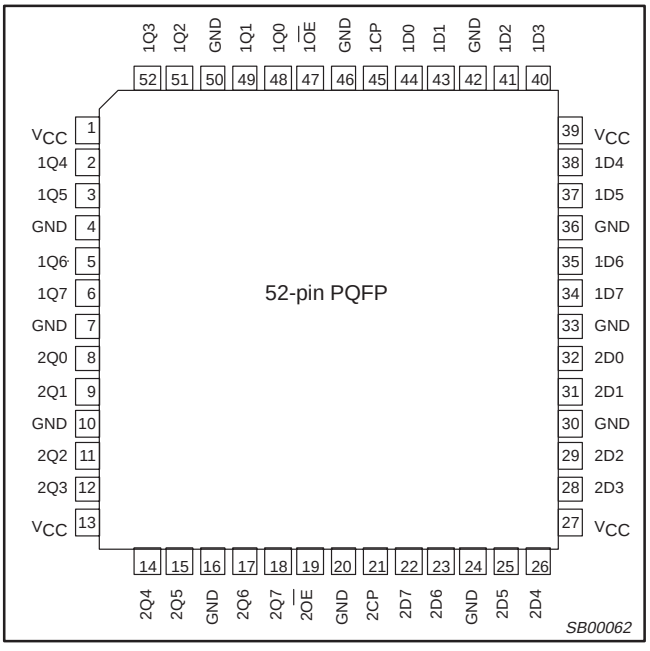
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS T_{amb} = 25°C; GND = 0V	TYPICAL	UNIT
t_{PLH} t_{PHL}	Propagation delay nCP to nQx	C_L = 50pF; V_{CC} = 5V	3.4 3.6	ns
C_{IN}	Input capacitance	V_I = 0V or V_{CC}	4	pF
C_{OUT}	Output capacitance	V_O = 0V or V_{CC}; 3-State	7	pF
I_{CCZ}	Total supply current	Outputs disabled; V_{CC} = 5.5V	120	µA

ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	DWG NUMBER
52–pin plastic Quad Flat Pack	–40°C to +85°C	MB2374 BB	MB2374 BB	SOT379-1

PIN CONFIGURATION

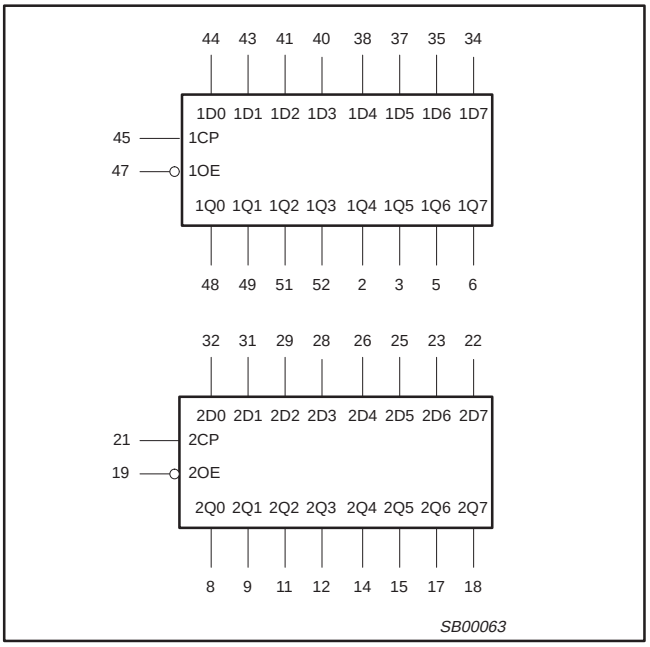


PIN DESCRIPTION

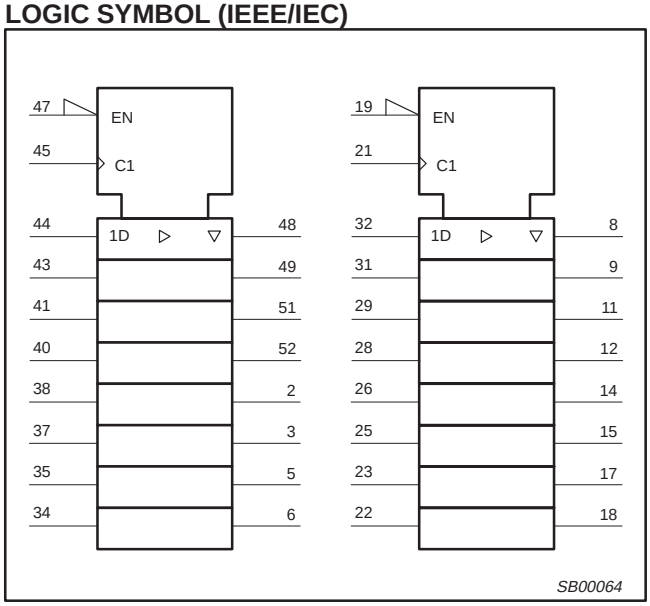
PIN NUMBER	SYMBOL	FUNCTION
44, 43, 41, 40, 38, 37, 35, 34, 32, 31, 29, 28, 26, 25, 23, 22	1D0 – 1D7 2D0 – 2D7	Data inputs
48, 49, 51, 52, 2, 3, 5, 6, 8, 9, 11, 12, 14, 15, 17, 18	1Q0 – 1Q7 2Q0 – 2Q7	Data outputs
47, 19	$1\overline{OE}$, $2\overline{OE}$	Output enable inputs (active-Low)
45, 21	1CP, 2CP	Clock pulse inputs (active rising edge)
4, 7, 10, 16, 20, 24, 30, 33, 36, 42, 46, 50	GND	Ground (0V)
1, 13, 27, 39	V_{CC}	Positive supply voltage

16-bit D-type flip-flop; positive-edge trigger (3-State) MB2374

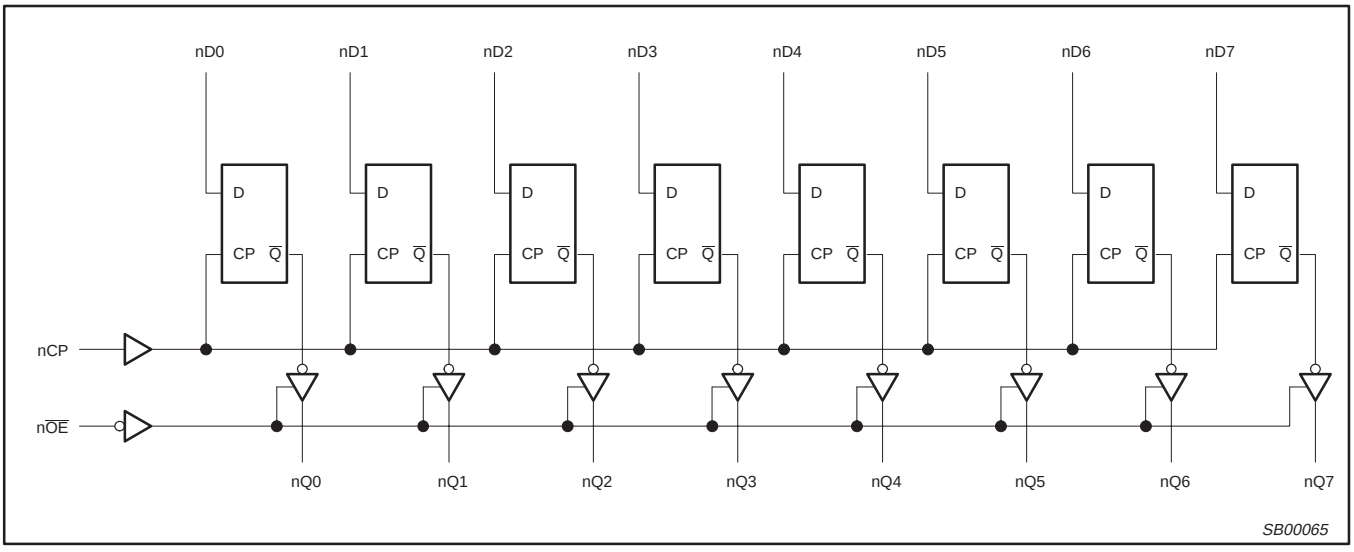
LOGIC SYMBOL



LOGIC SYMBOL (IEEE/IEC)



LOGIC DIAGRAM



FUNCTION TABLE

INPUTS			INTERNAL	OUTPUTS	OPERATING MODE
$n\overline{OE}$	nCP	nDx	REGISTER	nQ0 – nQ7	
L L	↑ ↑	l h	L H	L H	Load and read register
L	↥	X	NC	NC	Hold
H H	↥ ↑	X nDx	NC nDx	Z Z	Disable outputs

H = High voltage level
h = High voltage level one set-up time prior to the High-to-Low E transition
L = Low voltage level
l = Low voltage level one set-up time prior to the High-to-Low E transition
NC = No change
X = Don't care
Z = High impedance "off" state
↑ = Low-to-High clock transition
↥ = Not a Low-to-High clock transition

ABSOLUTE MAXIMUM RATINGS[1, 2]

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V_{CC}	DC supply voltage		–0.5 to +7.0	V
I_{IK}	DC input diode current	$V_I < 0$	–18	mA
V_I	DC input voltage[3]		–1.2 to +7.0	V
I_{OK}	DC output diode current	$V_O < 0$	–50	mA
V_{OUT}	DC output voltage[3]	output in Off or High state	–0.5 to +5.5	V
I_{OUT}	DC output current	output in Low state	128	mA
T_{stg}	Storage temperature range		–65 to 150	°C

NOTES:
1. Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
2. The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.
3. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIMITS		UNIT
		MIN	MAX	
V_{CC}	DC supply voltage	4.5	5.5	V
V_I	Input voltage	0	V_{CC}	V
V_{IH}	High-level input voltage	2.0		V
V_{IL}	Low-level Input voltage		0.8	V
I_{OH}	High-level output current		–32	mA
I_{OL}	Low-level output current		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	0	10	ns/V
T_{amb}	Operating free-air temperature range	–40	+85	°C

DC ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS					UNIT
			T_{amb} = +25°C			T_{amb} = –40°C to +85°C		
			MIN	TYP	MAX	MIN	MAX	
V_{IK}	Input clamp voltage	V_{CC} = 4.5V; I_{IK} = –18mA		–0.9	–1.2		–1.2	V
V_{OH}	High-level output voltage	V_{CC} = 4.5V; I_{OH} = –3mA; V_I = V_{IL} or V_{IH}	2.5	2.9		2.5		V
		V_{CC} = 5.0V; I_{OH} = –3mA; V_I = V_{IL} or V_{IH}	3.0	3.4		3.0		V
		V_{CC} = 4.5V; I_{OH} = –32mA; V_I = V_{IL} or V_{IH}	2.0	2.4		2.0		V
V_{OL}	Low-level output voltage	V_{CC} = 4.5V; I_{OL} = 64mA; V_I = V_{IL} or V_{IH}		0.42	0.55		0.55	V
V_{RST}	Power-up output voltage[3]	V_{CC} = 5.5V; I_O = 1mA; V_I = GND or V_{CC}		0.13	0.55		0.55	V
I_I	Input leakage current	V_{CC} = 5.5V; V_I = GND or 5.5V		±0.01	±1.0		±1.0	µA
I_{OFF}	Power-off leakage current	V_{CC} = 0.0V; V_O or $V_I \leq$ 4.5V		±5.0	±100		±100	µA
$I_{PU/PD}$	Power-up/down 3-State output current[4]	V_{CC} = 2.1V; V_O = 0.5V; V_I = GND or V_{CC}, V_{OE} = GND		±5.0	±50		±50	µA
I_{OZH}	3-State output High current	V_{CC} = 5.5V; V_O = 2.7V; V_I = V_{IL} or V_{IH}		5.0	50		50	µA
I_{OZL}	3-State output Low current	V_{CC} = 5.5V; V_O = 0.5V; V_I = V_{IL} or V_{IH}		–5.0	–50		–50	µA
I_{CEX}	Output High leakage current	V_{CC} = 5.5V; V_O = 5.5V; V_I = GND or V_{CC}		5.0	50		50	µA
I_O	Output current[1]	V_{CC} = 5.5V; V_O = 2.5V	–50	–70	–180	–50	–180	mA
I_{CCH}	Quiescent supply current	V_{CC} = 5.5V; Outputs High, V_I = GND or V_{CC}		120	250		250	µA
I_{CCL}		V_{CC} = 5.5V; Outputs Low, V_I = GND or V_{CC}		48	60		60	mA
I_{CCZ}		V_{CC} = 5.5V; Outputs 3-State; V_I = GND or V_{CC}		120	250		250	µA
ΔI_{CC}	Additional supply current per input pin[2]	V_{CC} = 5.5V; one input at 3.4V, other inputs at V_{CC} or GND		0.5	1.5		1.5	mA

NOTES:
1. Not more than one output should be tested at a time, and the duration of the test should not exceed one second.
2. This is the increase in supply current for each input at 3.4V.
3. For valid test results, data must not be loaded into the flip-flops (or latches) after applying the power.
4. This parameter is valid for any V_{CC} between 0V and 2.1V with a transition time of up to 10msec. From V_{CC} = 2.1V to V_{CC} = 5V ± 10% a transition time of up to 100µsec is permitted.

AC CHARACTERISTICS

GND = 0V, $t_R = t_F$ = 2.5ns, C_L = 50pF, R_L = 500Ω

SYMBOL	PARAMETER	WAVEFORM	LIMITS					UNIT
			T_{amb} = +25°C V_{CC} = +5.0V			T_{amb} = -40 to +85°C V_{CC} = +5.0V ±0.5V		
			MIN	TYP	MAX	MIN	MAX	
f_{MAX}	Maximum clock frequency	1	180	260		180		MHz
t_{PLH} t_{PHL}	Propagation delay nCP to nQx	1	1.8 1.8	3.4 3.6	4.6 4.6	1.8 1.8	5.1 5.1	ns
t_{PZH} t_{PZL}	Output enable time to High and Low level	3 4	1.2 2.1	3.0 4.0	4.1 5.5	1.2 2.1	4.8 6.2	ns
t_{PHZ} t_{PLZ}	Output disable time from High and Low level	3 4	1.2 1.8	3.4 3.6	4.6 5.0	1.2 1.8	5.1 5.5	ns

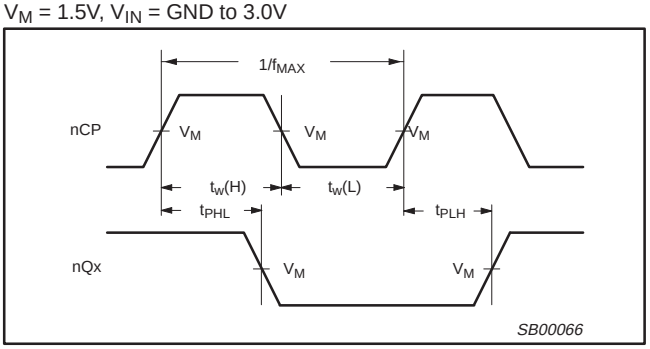
AC SETUP REQUIREMENTS

GND = 0V, $t_R = t_F$ = 2.5ns, C_L = 50pF, R_L = 500Ω

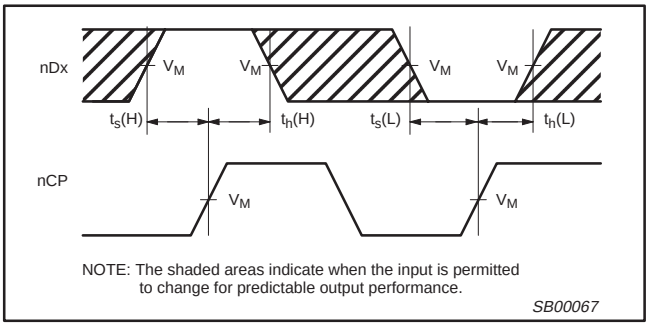
SYMBOL	PARAMETER	WAVEFORM	LIMITS			UNIT
			T_{amb} = +25°C, V_{CC} = +5.0V		T_{amb} = -40 to +85°C, V_{CC} = +5.0V ±0.5V	
			MIN	TYP	MIN	
$t_s(H)$ $t_s(L)$	Setup time, High or Low nDx to nCP	2	1.0 1.0	0.3 0.1	1.0 1.0	ns
$t_h(H)$ $t_h(L)$	Hold time, High or Low nDx to nCP	2	1.0 1.0	–0.1 –0.3	1.0 1.0	ns
$t_w(H)$ $t_w(L)$	nCP pulse width High or Low	1	2.8 2.8	1.2 1.5	2.8 2.8	ns

AC WAVEFORMS

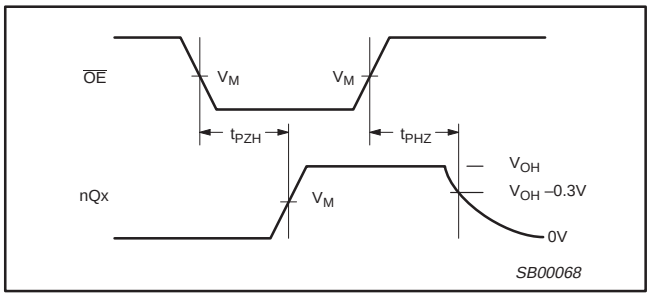
V_M = 1.5V, V_{IN} = GND to 3.0V



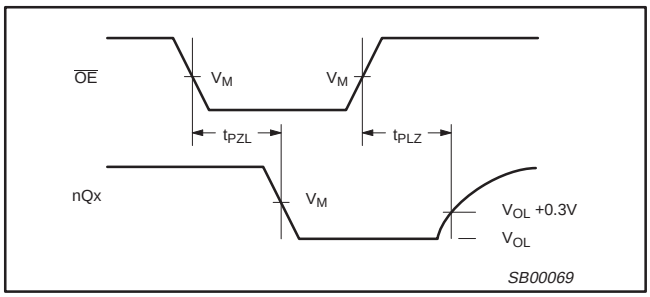
Waveform 1. Propagation Delay, Clock Input to Output, Clock Pulse Width, and Maximum Clock Frequency



Waveform 2. Data Setup and Hold Times

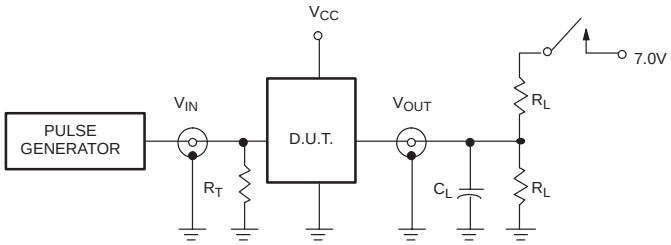


Waveform 3. 3–State Output Enable Time to High Level and Output Disable Time from High Level

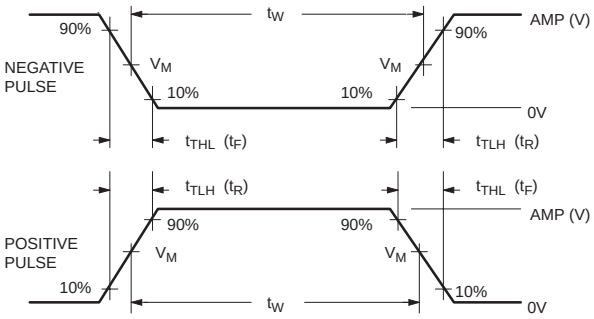


Waveform 4. 3–State Output Enable Time to Low Level and Output Disable Time from Low Level

TEST CIRCUIT AND WAVEFORM



Test Circuit for 3-State Outputs



V_M = 1.5V
Input Pulse Definition

SWITCH POSITION

TEST	SWITCH
t_{PLZ}	closed
t_{PZL}	closed
All other	open

DEFINITIONS

R_L = Load resistor; see AC CHARACTERISTICS for value.

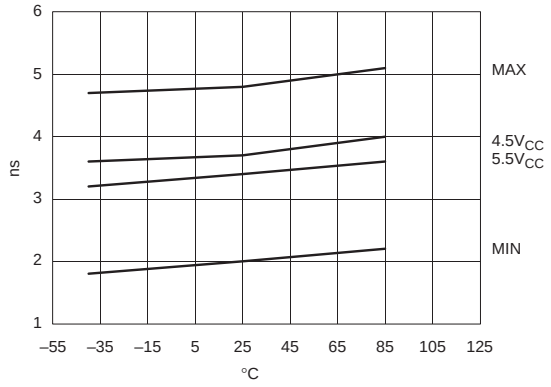
C_L = Load capacitance includes jig and probe capacitance; see AC CHARACTERISTICS for value.

R_T = Termination resistance should be equal to Z_{OUT} of pulse generators.

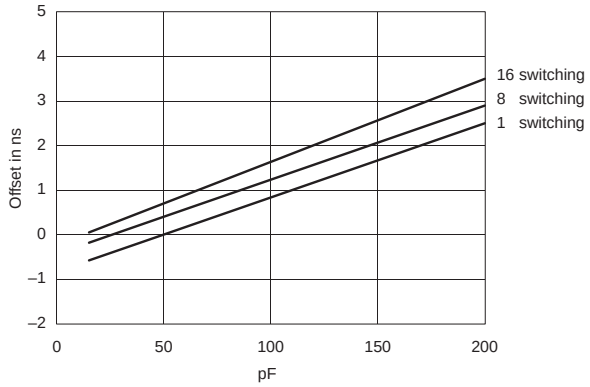
FAMILY	INPUT PULSE REQUIREMENTS				
	Amplitude	Rep. Rate	t_W	t_R	t_F
MB	3.0V	1MHz	500ns	2.5ns	2.5ns

SB00010

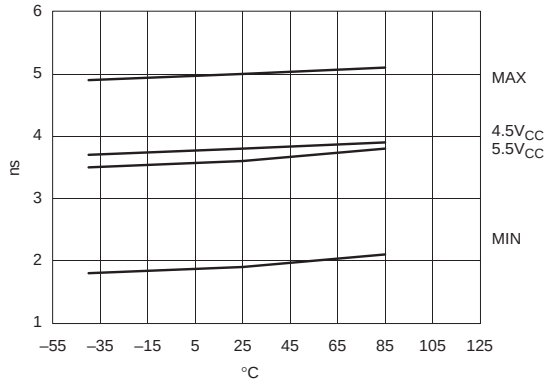
t_{PLH} vs Temperature (T_{amb})
C_L = 50pF, 1 Output Switching
nCP to nQx



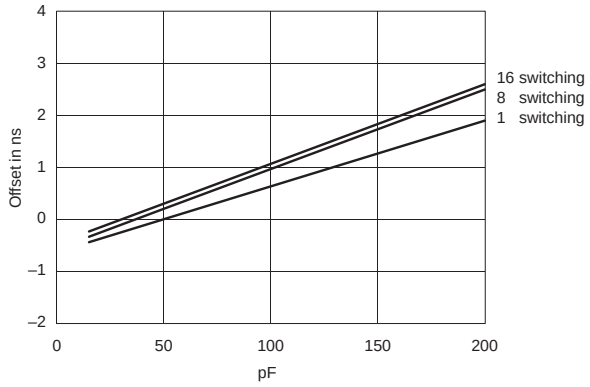
Adjustment of t_{PLH} for
Load Capacitance and # of Outputs Switching
nCP to nQx



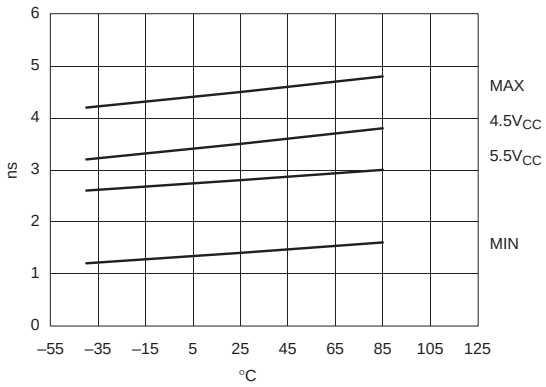
t_{PHL} vs Temperature (T_{amb})
C_L = 50pF, 1 Output Switching
nCP to nQx



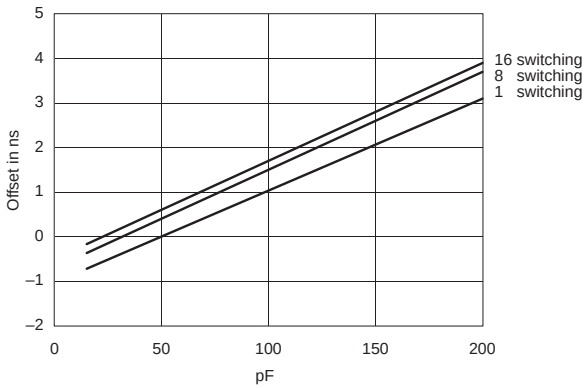
Adjustment of t_{PHL} for
Load Capacitance and # of Outputs Switching
nCP to nQx



t_{PZH} vs Temperature (T_{amb})
C_L = 50pF, 1 Output Switching
n$\overline{OE}$ to nQx

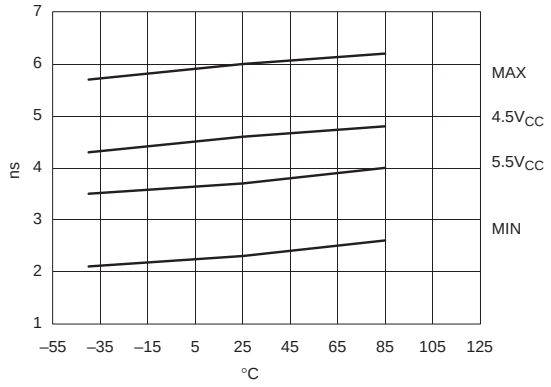


Adjustment of t_{PZH} for
Load Capacitance and # of Outputs Switching
n$\overline{OE}$ to nQx

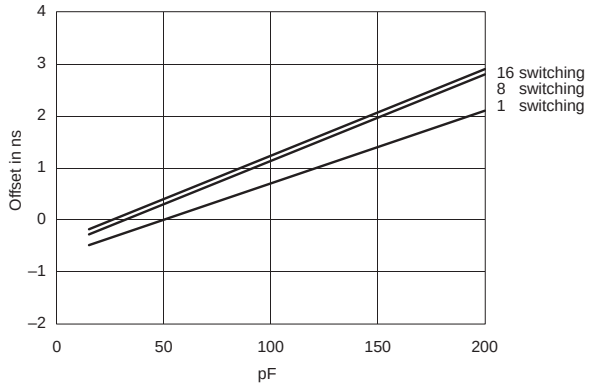


SB00070

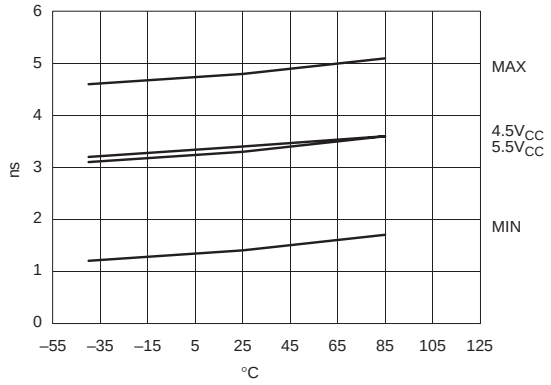
t_{PZL} vs Temperature (T_{amb})
C_L = 50pF, 1 Output Switching
n$\overline{OE}$ to nQx



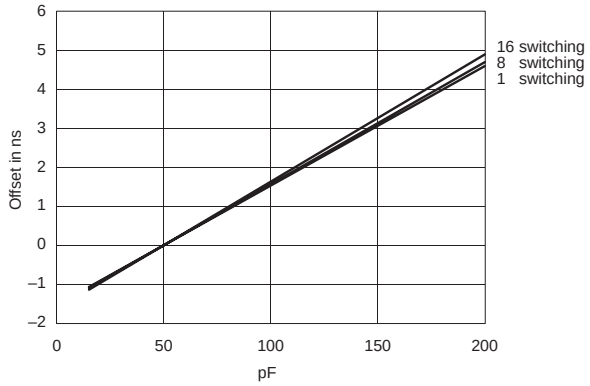
Adjustment of t_{PZL} for
Load Capacitance and # of Outputs Switching
n$\overline{OE}$ to nQx



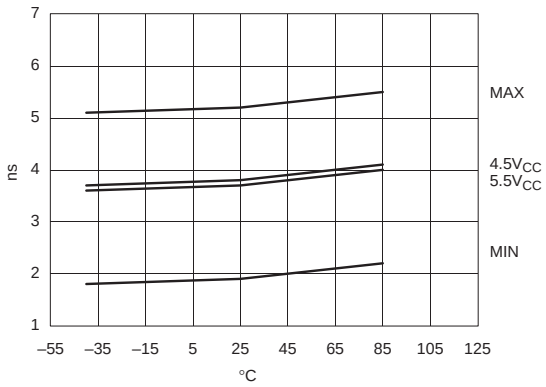
t_{PHZ} vs Temperature (T_{amb})
C_L = 50pF, 1 Output Switching
n$\overline{OE}$ to nQx



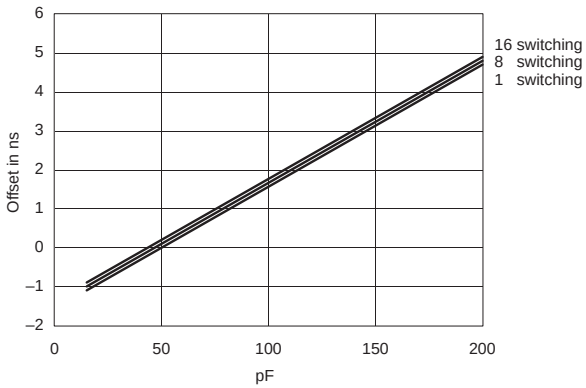
Adjustment of t_{PHZ} for
Load Capacitance and # of Outputs Switching
n$\overline{OE}$ to nQx



t_{PLZ} vs Temperature (T_{amb})
C_L = 50pF, 1 Output Switching
n$\overline{OE}$ to nQx

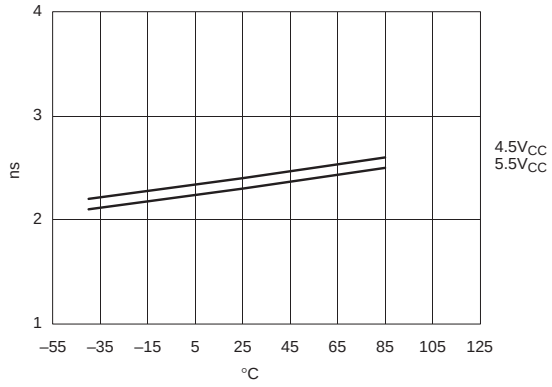


Adjustment of t_{PLZ} for
Load Capacitance and # of Outputs Switching
n$\overline{OE}$ to nQx

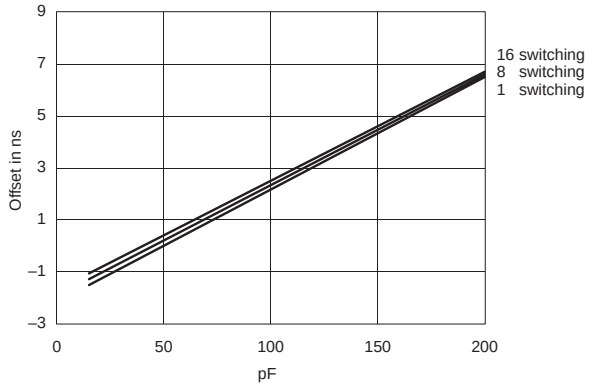


SB00071

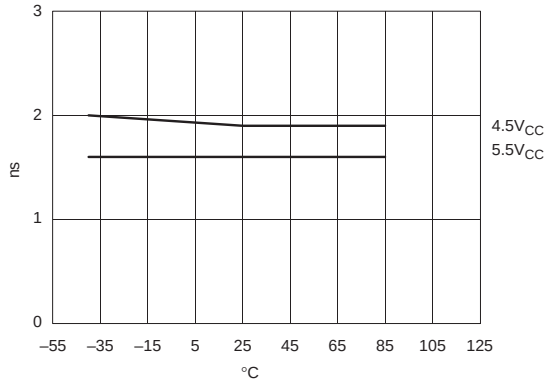
t_{TLH} vs Temperature (T_{amb})
C_L = 50pF, 1 Output Switching



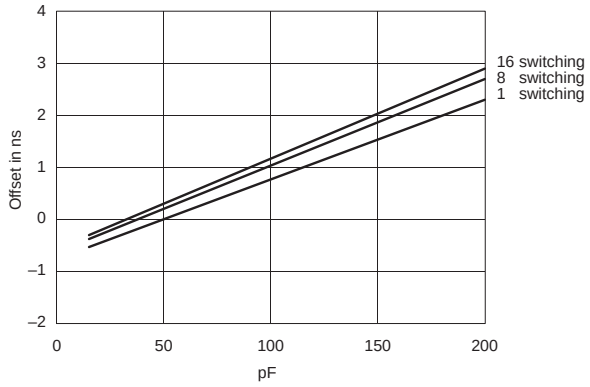
Adjustment of t_{TLH} for
Load Capacitance/# of Outputs



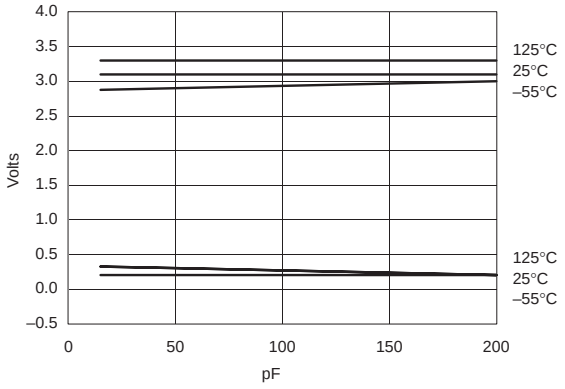
t_{THL} vs Temperature (T_{amb})
C_L = 50pF, 1 Output Switching



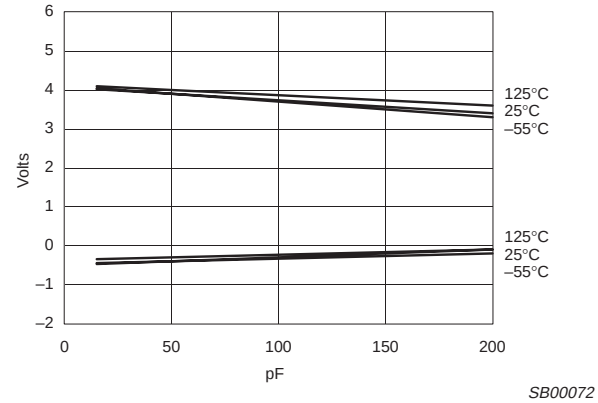
Adjustment of t_{THL} for
Load Capacitance and # of Outputs Switching



V_{OHV} and V_{OLP} vs Load Capacitance
V_{CC} = 5V, V_{IN} = 0 to 3V

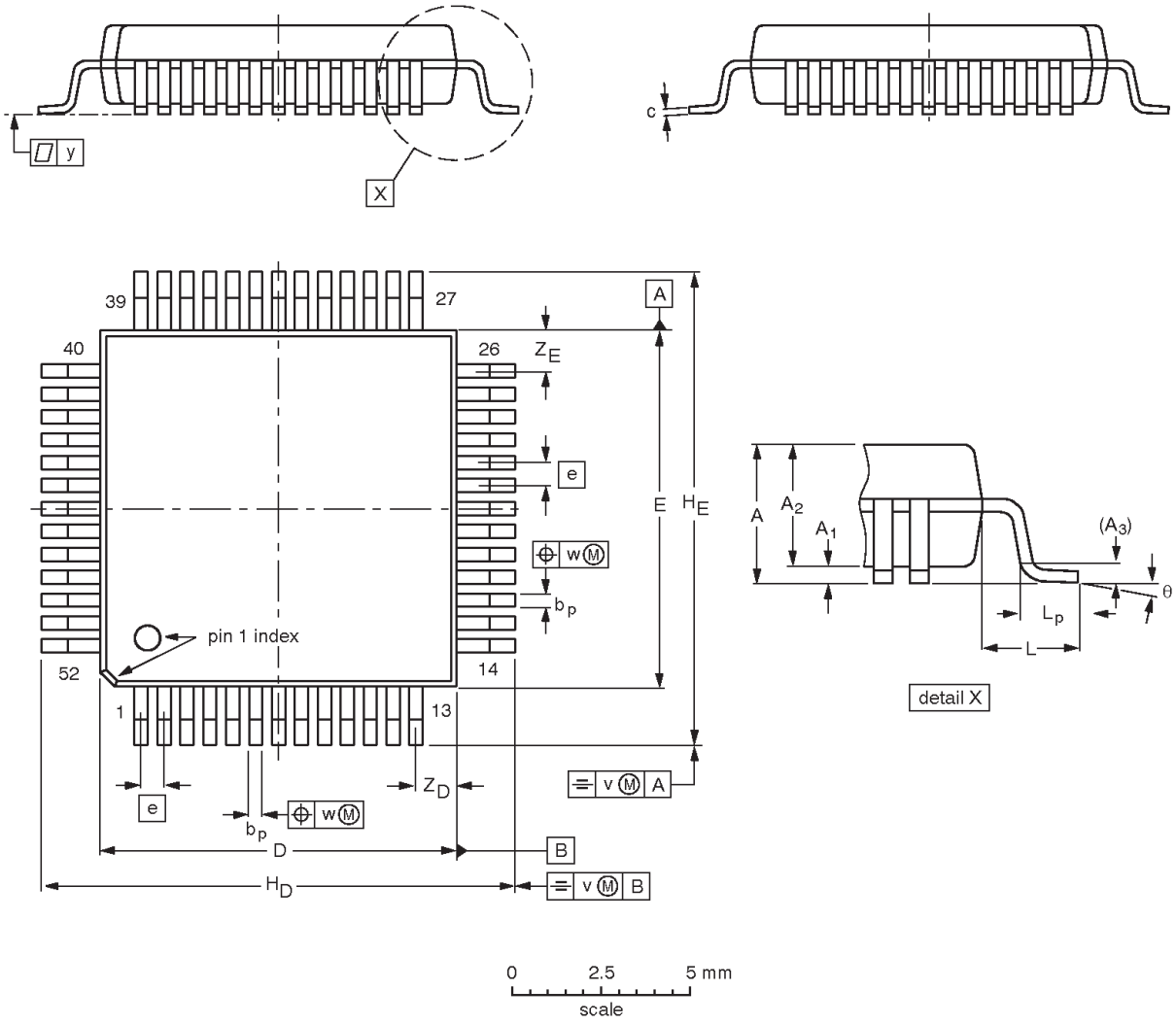


V_{OHP} and V_{OLV} vs Load Capacitance
V_{CC} = 5V, V_{IN} = 0 to 3V



SB00072

QFP52: plastic quad flat package; 52 leads (lead length 1.6 mm); body 10 x 10 x 2.0 mm SOT379-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_D	H_E	L	L_p	v	w	y	$Z_D^{(1)}$	$Z_E^{(1)}$	θ
mm	2.45	0.45 0.25	2.10 1.95	0.25	0.38 0.22	0.23 0.13	10.1 9.9	10.1 9.9	0.65	13.45 12.95	13.45 12.95	1.60	0.95 0.65	0.20	0.12	0.10	1.24 0.95	1.24 0.95	7^o 0^o

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT379-1		MO-108				~~95-02-04~~ 97-08-04

Dual octal D-type flip-flop; positive-edge trigger (3-State)

MB2374

Data sheet status

Data sheet status	Product status	Definition [1]
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make chages at any time without notice in order to improve design and supply the best possible product.
Product specification	Production	This data sheet contains final specifications. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.

[1] Please consult the most recently issued datasheet before initiating or completing a design.

Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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